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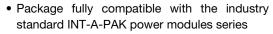
Vishay Semiconductors

Three Phase Controlled Bridge (Power Modules), 55 A to 110 A



PRODUCT SUMMARY					
I _O	55 A to 110 A				
V_{RRM}	800 V to 1600 V				
Package	MT-K				
Circuit	Three phase bridge				

FEATURES





- High thermal conductivity package, electrically insulated case
- Excellent power volume ratio
- 4000 V_{RMS} isolating voltage
- UL E78996 approved
- Designed and qualified for industrial level
- Material categorization: For definitions of com-
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION

A range of extremely compact, encapsulated three phase controlled bridge rectifiers offering efficient and reliable operation. They are intended for use in general purpose and heavy duty applications.

MAJOR RATINGS AND CHARACTERISTICS								
SYMBOL	CHARACTERISTICS	VALUES 5.MTK	VALUES 9.MTK	VALUES 11.MTK	UNITS			
1		55	90	110	Α			
Io	T _C	85	85	85	°C			
1	50 Hz	390	950	1130				
I _{FSM}	60 Hz	410	1000	1180	Α			
l ² t	50 Hz	770	4525	6380	A2-			
1-1	60 Hz	700	4130	5830	A ² s			
$I^2\sqrt{t}$		7700	45 250	63 800	A²√s			
V _{RRM}	Range		V					
T _{Stg}	Range	-40 to 125 °C						
TJ	Range		-40 to 125		°C			

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE V _{RRM} , MAXIMUM REPETITIVE PEA CODE REVERSE VOLTA V		V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM REPETITIVE PEAK OFF-STATE VOLTAGE, GATE OPEN CIRCUIT V	I _{RRM} /I _{DRM} , MAXIMUM AT T _J = 125 °C mA			
	80	800	900	800				
	100	1000	1100	1000				
VS-5.MTK	120	1200	1300	1200	10			
	140	1400	1500	1400				
	160	1600	1700	1600				
	80	800	900	800				
VS-9.MTK	100	1000	1100	1000				
VS-9.IVITK VS-11.MTK	120	1200	1300	1200	20			
V3-11.W11K	140	1400	1500	1400				
	160	1600	1700	1600				

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FORWARD CONDUCTIO	N							
PARAMETER	SYMBOL		TEST CONI	VALUES 5.MTK	VALUES 9.MTK	VALUES 11.MTK	UNITS	
Maximum DC output current at	I _O	120° rect	conduction and	rle	55	90	110	Α
case temperature	.0	120 1001.	oonaaonon ang		85	85	85	°C
		t = 10 ms	No voltage		390	950	1130	
Maximum peak, one-cycle forward, non-repetitive on state	I _{TSM}	t = 8.3 ms	reapplied		410	1000	1180	Α
surge current	TISM	t = 10 ms	$100\%V_{RRM}$		330	800	950	
		t = 8.3 ms	reapplied	Initial $T_{.1} = T_{.1}$ max.	345	840	1000	
		t = 10 ms	No voltage	illida ij = ijillax.	770	4525	6380	
Maximum I ² t for fusing	l ² t	t = 8.3 ms	reapplied		700	4130	5830	A ² s
Maximum I-t for fusing	1-1	t = 10 ms	100 % V _{RRM}		540	3200	4510	
		t = 8.3 ms reapplied		500	2920	4120	1	
Maximum I ² √t for fusing	I ² √t	t = 0.1 ms	to 10 ms, no v	oltage reapplied	7700	45 250	63 800	A ² √s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x 1	(16.7 % x π x I _{T(AV)} < I < π x I _{T(AV)} , T _J maximum			1.09	1.04	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(A)})$	_{V)}), T _J maximun	1.45	1.27	1.27	V	
Low level value on-state slope resistance	r _{t1}	(16.7 % x a	$π x I_{T(AV)} < I < π$	12.40	4.10	3.93	mΩ	
High level value on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)})$, T_J maximum			11.04	3.59	3.37	11152
Maximum on-state voltage drop	V_{TM}	$I_{pk} = 150 A$	I_{pk} = 150 A, T_J = 25 °C, t_p = 400 μ s single junction			1.65	1.57	V
Maximum non-repetitve rate of rise of turned on current	dl/dt	$T_J = 25$ °C, from 0.67 V_{DRM} , $I_{TM} = \pi \times I_{T(AV)}$, $I_g = 500$ mA, $t_r < 0.5$ μ s, $t_p > 6$ μ s				150		A/µs
Maximum holding current	I _H	T _J = 25 °C gate open		= 6 V, resistive load,		200		mA
Maximum latching current	ΙL	$T_J = 25 ^{\circ}\text{C}$, anode supply	= 6 V, resistive load		400		

BLOCKING						
PARAMETER	SYMBOL	TEST CONDITIONS	5.MTK	9.MTK	11.MTK	UNITS
RMS isolation voltage	V_{ISOL}	$T_J = 25$ °C all terminal shorted, f = 50 Hz, t = 1 s		4000		V
Maximum critical rate of rise of off-state voltage	dV/dt (1)	$T_J = T_J$ maximum, linear to 0.67 V_{DRM} , gate open circuit	500		V/µs	

Note

 $^{(1)}$ Available with dV/dt = 1000 V/ μ s, to complete code add S90 i. e. 113MT160KBS90

TRIGGERING							
PARAMETER	SYMBOL	TEST CONDITIONS 5.MTK 9.MTK 11.MTK				11.MTK	UNITS
Maximum peak gate power	P _{GM}				10		W
Maximum average gate power	P _{G(AV)}				2.5		VV
Maximum peak gate current	I_{GM}	$T_J = T_J$ maximum			2.5		Α
Maximum peak negative gate voltage	- V _{GT}		10				
		T _J = - 40 °C		4.0			V
Maximum required DC gate voltage to trigger	V_{GT}	T _J = 25 °C	Anode supply = 6 V,	2.5			
voltage to trigger		T _J = 125 °C		1.7			
		T _J = - 40 °C	resistive load	270 150 80			
Maximum required DC gate current to trigger	I _{GT}	T _J = 25 °C					mA
ouncin to ingger		T _J = 125 °C					
Maximum gate voltage that will not trigger	V_{GD}	T. – T. maximum, rator	0.25		V		
Maximum gate current that will not trigger	I _{GD}	$T_J = T_J$ maximum, rated V_{DRM} applied 6					mA

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PARAMETER	SYMBOL	TEST CONDITIONS	5.MTK	9.MTK	11.MTK	UNITS		
Maximum junction operating and storage temperature range	T _J , T _{Stg}		- 40 to 125			°C		
		DC operation per module	0.18	0.14	0.12			
Maximum thermal resistance,	Б	DC operation per junction	1.07	0.86	0.70			
junction to case	R_{thJC}	120 °C rect. conduction angle per module	0.19	0.15	0.12	K/W		
		120 °C rect. conduction angle per junction	1.17	0.91	0.74	† ~ W		
Maximum thermal resistance, case to heatsink per module	R _{thCS}	Mounting surface smooth, flat and grased	0.03					
Mounting to heatsink		A mounting compound is recommended and 4 to 6			Nim			
torque ± 10 % to terminal		the torque should be rechecked after a period of	f 3 to 4			Nm		
Approximate weight		3 hours to allow for the spread of the compound. Lubricated threads.	225		g			

∆R CONDU	△R CONDUCTION PER JUNCTION										
DEVICES	SINUSOIDAL CONDUCTION AT T _J MAXIMUM					RECTANGULAR CONDUCTION AT T _J MAXIMUM					UNITS
	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	,
5.MTK	0.072	0.085	0.108	0.152	0.233	0.055	0.091	0.117	0.157	0.236	
9.MTK	0.033	0.039	0.051	0.069	0.099	0.027	0.044	0.055	0.071	0.100	K/W
11.MTK	0.027	0.033	0.042	0.057	0.081	0.023	0.037	0.046	0.059	0.082	

Note

Table shows the increment of thermal resistance RthJC when devices operate at different conduction angles than DC

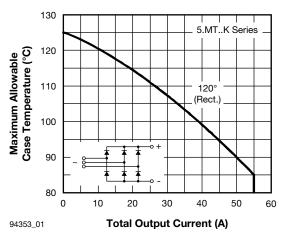


Fig. 1 - Current Ratings Characteristic

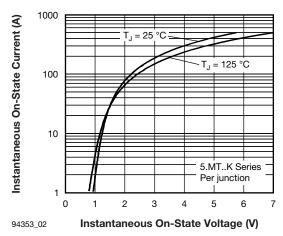
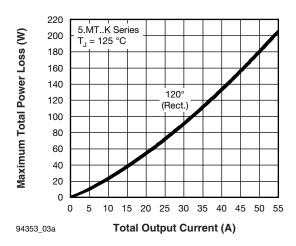


Fig. 2 - Forward Voltage Drop Characteristics

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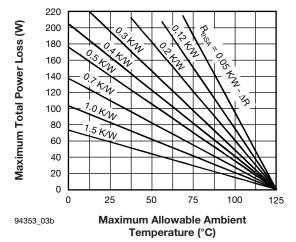


Fig. 3 - Total Power Loss Characteristics

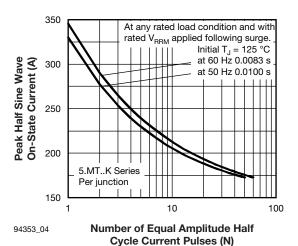


Fig. 4 - Maximum Non-Repetitive Surge Current

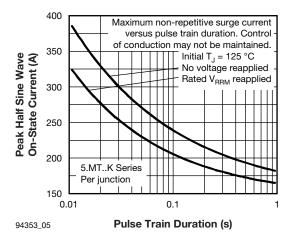


Fig. 5 - Maximum Non-Repetitive Surge Current

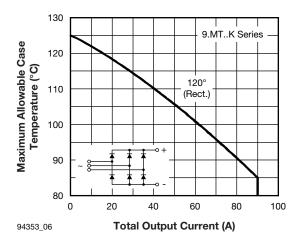


Fig. 6 - Current Ratings Characteristic

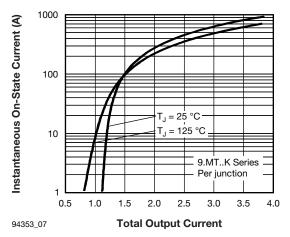
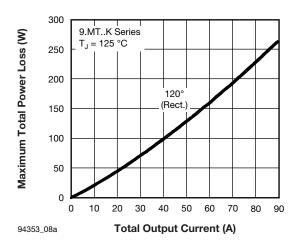


Fig. 7 - Forward Voltage Drop Characteristics



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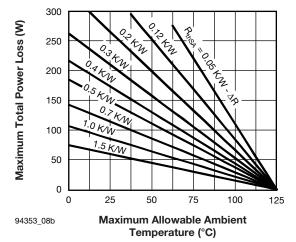


Fig. 8 - Total Power Loss Characteristics

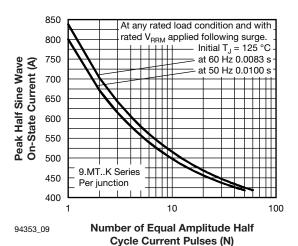


Fig. 9 - Maximum Non-Repetitive Surge Current

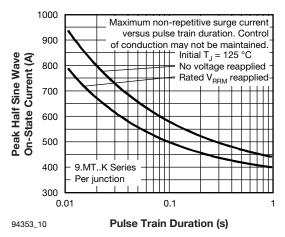


Fig. 10 - Maximum Non-Repetitive Surge Current

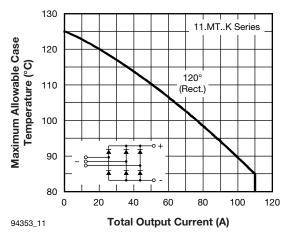


Fig. 11 - Current Ratings Characteristic

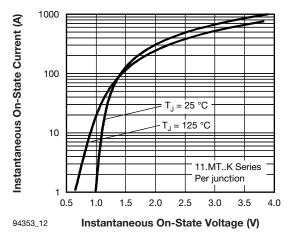
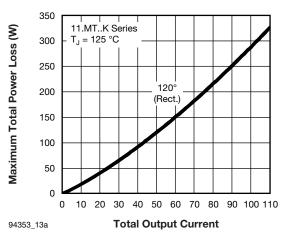


Fig. 12 - Forward Voltage Drop Characteristics

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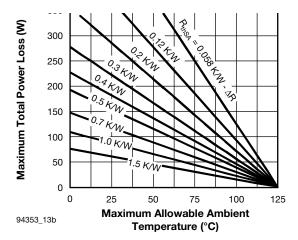


Fig. 13 - Total Power Loss Characteristics

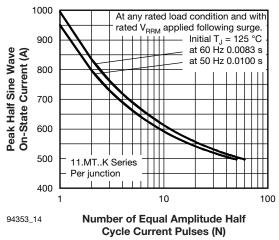


Fig. 14 - Maximum Non-Repetitive Surge Current

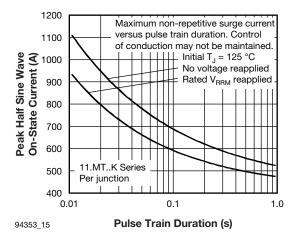


Fig. 15 - Maximum Non-Repetitive Surge Current

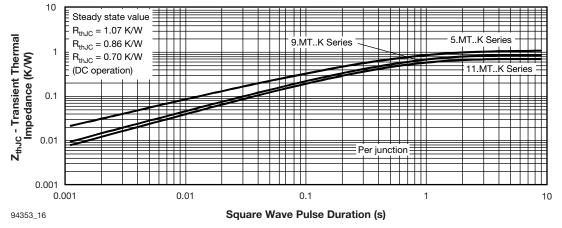


Fig. 16 - Thermal Impedance Z_{thJC} Characteristics

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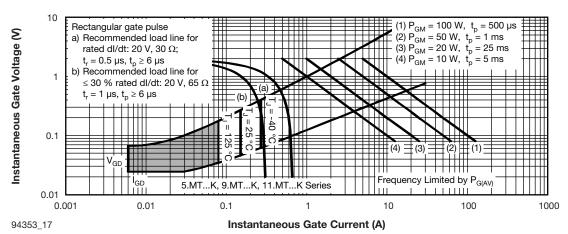
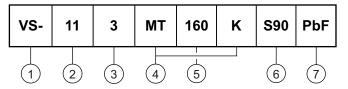


Fig. 17 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code

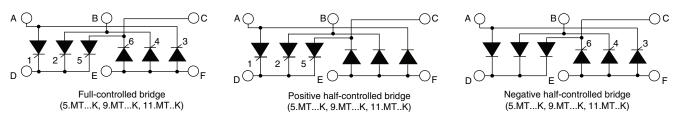


- Vishay Semiconductors product
- 2 Current rating code:
 - 5 = 55 A (average)
 - 9 = 90 A (average)
 - 11 = 110 A (average)
- 3 Circuit configuration code:
 - 1 = Negative half-controlled bridge
 - 2 = Positive half-controlled bridge
 - 3 = Full-controlled bridge
- 4 Essential part number
- 5 Voltage code x 10 = V_{RRM} (see Voltage Ratings table)
- 6 Critical dV/dt:
 - None = 500 V/µs (standard value)
 - S90 = 1000 V/µs (special selection)
- 7 PbF = Lead (Pb)-free

Note

To order the optional hardware go to www.vishay.com/doc?95172

CIRCUIT CONFIGURATION



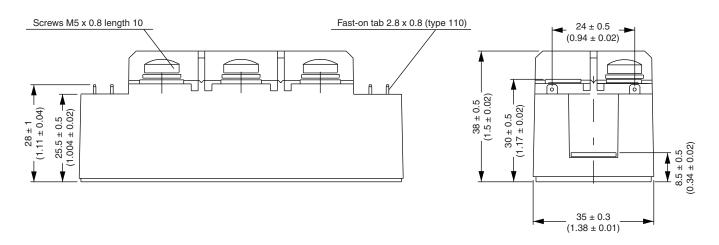
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95004				

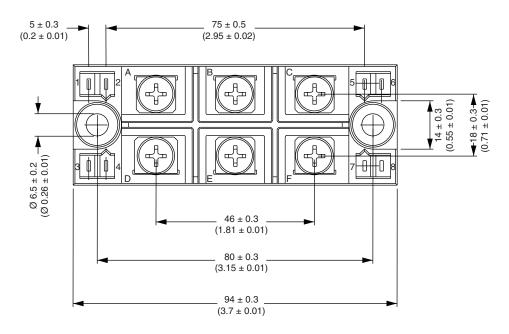


Vishay Semiconductors

MTK (with and without optional barrier)

DIMENSIONS WITH OPTIONAL BARRIERS in millimeters (inches)

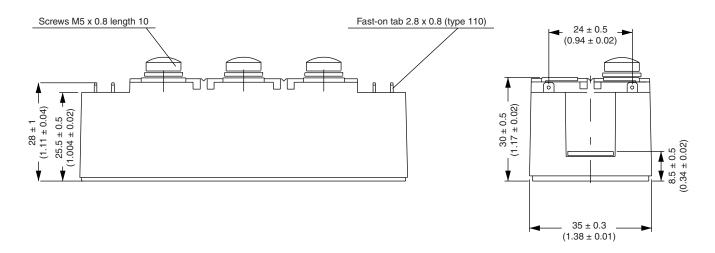


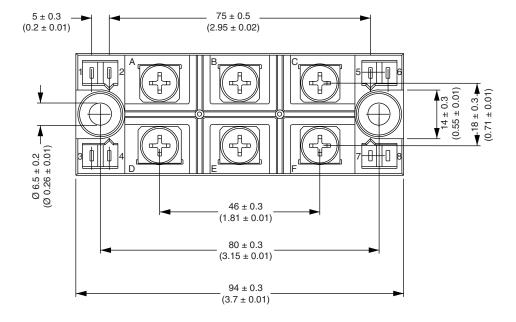


Vishay Semiconductors MTK (with and without optional barrier)



DIMENSIONS WITHOUT OPTIONAL BARRIERS in millimeters (inches)







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Revision: 02-Oct-12 Document Number: 91000

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